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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/711,473	09/21/2004	Hsi-Ming Chang	Hsi-Ming Chang 13530-US-PA	
	7590 01/05/2007 N INTELLECTUAL PRO	EXAMINER		
7 FLOOR-1, N	O. 100	ERDEM, FAZLI		
ROOSEVELT TAIPEI, 100	ROAD, SECTION 2	ART UNIT	PAPER NUMBER	
TAIWAN		2826		
SHORTENED STATUTOR	Y PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE	
3 MO	NTHS	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

· ·			Application No.	Applicant(s)				
Office Action Summary		10/711,473	CHANG, HSI-MING					
			Examiner	Art Unit	·			
			Fazli Erdem	2826				
Period fo	The MAILING DATE of this commun or Reply	ication appe	ears on the cover sheet with the	correspondence addre	ess			
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR CHEVER IS LONGER, FROM THE MINIORS of time may be available under the provisions SIX (6) MONTHS from the mailing date of this common period for reply is specified above, the maximum state to reply within the set or extended period for reply reply received by the Office later than three months are depatent term adjustment. See 37 CFR 1.704(b).	AILING DA of 37 CFR 1.136 nunication. atutory period will will, by statute, of	TE OF THIS COMMUNICATIO 6(a). In no event, however, may a reply be ti Il apply and will expire SIX (6) MONTHS fror cause the application to become ABANDON	N. mely filed n the mailing date of this comm ED (35 U.S.C. § 133).				
Status				•				
1)🛛	Responsive to communication(s) file	ed on <i>18 Oc</i>	tober 2006					
2a)□	This action is <b>FINAL</b> . 2b)⊠ This action is non-final.							
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is							
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.							
Dispositi	ion of Claims							
4) 🔯	4)⊠ Claim(s) <u>1-19</u> is/are pending in the application.							
-	4a) Of the above claim(s) is/are withdrawn from consideration.							
	Claim(s) is/are allowed.							
6)🛛	Claim(s) <u>1-19</u> is/are rejected.							
7)	_							
8)	Claim(s) are subject to restric	tion and/or	election requirement.					
Applicati	on Papers							
9)[]	The specification is objected to by the	e Examiner.	•					
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.								
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).								
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.								
Priority ι	ınder 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) □ All b) □ Some * c) □ None of:								
/-	1. Certified copies of the priority documents have been received.							
	2. Certified copies of the priority documents have been received in Application No							
	3. Copies of the certified copies of the priority documents have been received in this National Stage							
	application from the International Bureau (PCT Rule 17.2(a)).							
* See the attached detailed Office action for a list of the certified copies not received.								
Attachment	(s)							
1) Notice of References Cited (PTO-892)  4) Interview Summary (PTO-413)								
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)			Paper No(s)/Mail D	ate				
	nation Disclosure Statement(s) (PTO/SB/08)  No(s)/Mail Date		5) Notice of Informal F	ratent Application				
•	<del></del>		, <del>_</del>					

## **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

2. Claims 1-19 rejected under 35 U.S.C. 102(e) as being anticipated by Takeashi et al. (6,624,473).

Regarding Claim 1, Takehashi et al. disclose a thin-film transistor, panel and methods for producing the same where in Fig. 3, 10B, 21 and in claim 1 it is disclosed a substrate 10, a polysilicon layer 1 disposed over the substrate, polysilicon layer comprising source and drain regions 150/160 and lightly doped source/drain regions 152/262 between the channel region 170 and the source/drain region, a gate insulation layer 2disposed over the substrate covering the channel region and the lightly doped drain region, a gate buffer layer 42 disposed over the gate insulation layer covering the channel layer and the lightly doped region, a gate 41 disposed over the gate buffer layer, wherein the gate buffer layer 42 is disposed between the gate 41 and the gate insulation layer 2, a dielectric layer 3 arranged over the gate, a source/drain metal layers 5/6, disposed over the dielectric layer 3, and connected to the source/drain regions 150/160.

Regarding Claim 2, in claim 1 of Takehashi et al. the gate layer is disclosed to be metal.

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Regarding Claim 3, in claim 1 of Takehashi et al. the gate buffer layer below the gate layer is disclosed to the a metallic compound, i.e. a metal silicide.

Regarding Claim 4, in Fig. 23, sides of the lower gate electrode, i.e. gate buffer layer could be anodized, i.e. a metal oxide.

Regarding Claims 5 and 7, as Figs 10b and 19 suggest, gate buffer layer, i.e. lower electrode has a lower metal content near the gate insulation film 2:

Regarding Claim 6 and 8, as Figs. 10b and 19 suggest, gate buffer layer, i.e. lower gate electrode has a dopant containing material.

Regarding Claims 9 and 10, Fig. 3 disclose the ladder and taped shaped buffer layer.

Regarding Claim 11, buffer layer 12 is arranged between the substrate and the polysilicon layer.

Regarding Claims 12, 13 and 18, manufacturing steps are disclosed in Fig. 19, 23, 24 and 29.

Regarding Claim 14, in Fig. 4 and 5, sputtering method was used.

Regarding Claim 15 and 16, column 8, lines 1-10 the required gas type is disclosed.

Regarding Claim 19, in Fig. 21, the gate buffer layer, i.e. lower gate electrode layer 42, is disposed over the lightly doped regions but not the source/drain regions.

## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would

like assistance from a USPTO Customer Service Representative or access to the automated

information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

FE

December 17, 2006

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